



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- $BV_{CEO} > -150V$
- $I_C = -1A$ Continuous Current
- $I_{CM} = -2A$ Peak Pulse Current
- Complementary NPN Type: DIODES™ NK-FZT655

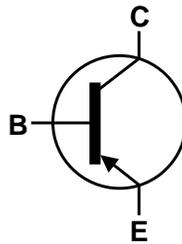
Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208③
- Weight: 0.112 grams (Approximate)

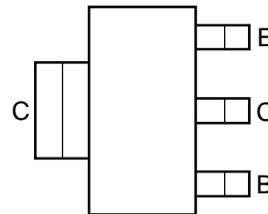
SOT223



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CB0} | -150 | V |
| Collector-Emitter Voltage | V _{CEO} | -150 | V |
| Emitter-Base Voltage | V _{EBO} | -7 | V |
| Continuous Collector Current | I _C | -1 | A |
| Peak Pulse Current | I _{CM} | -2 | A |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

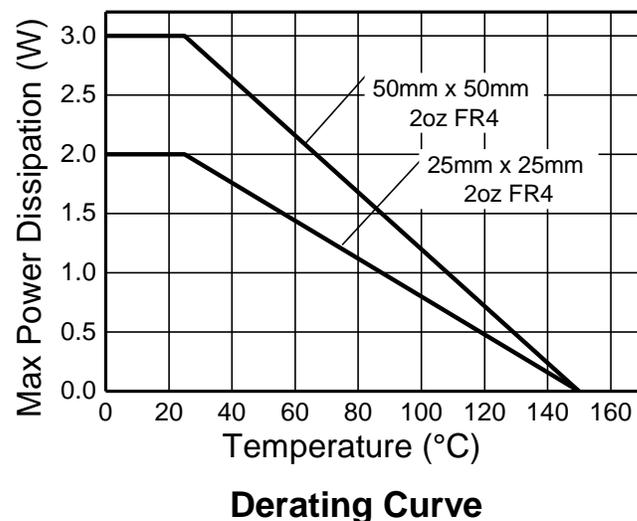
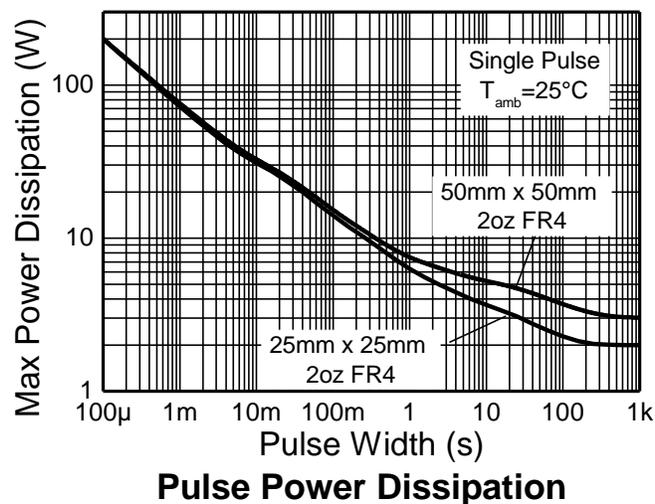
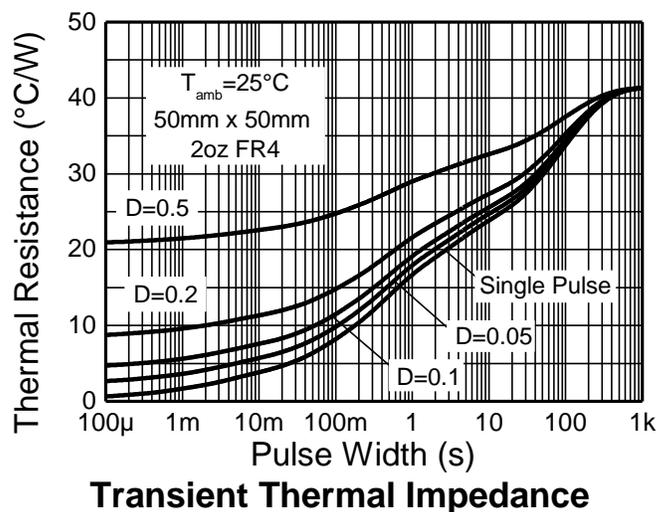
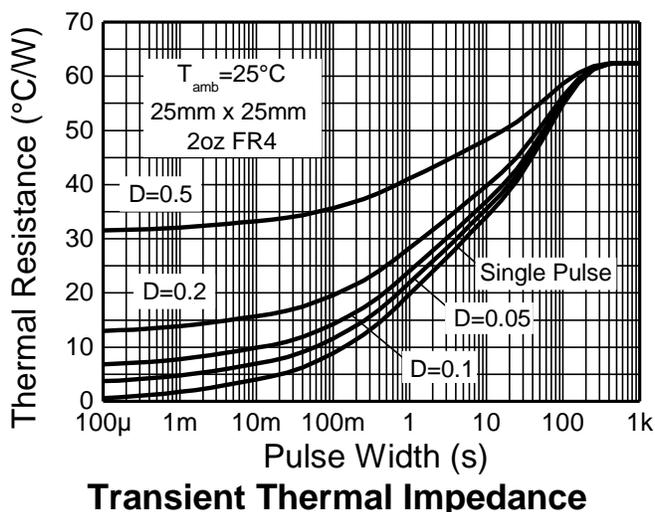
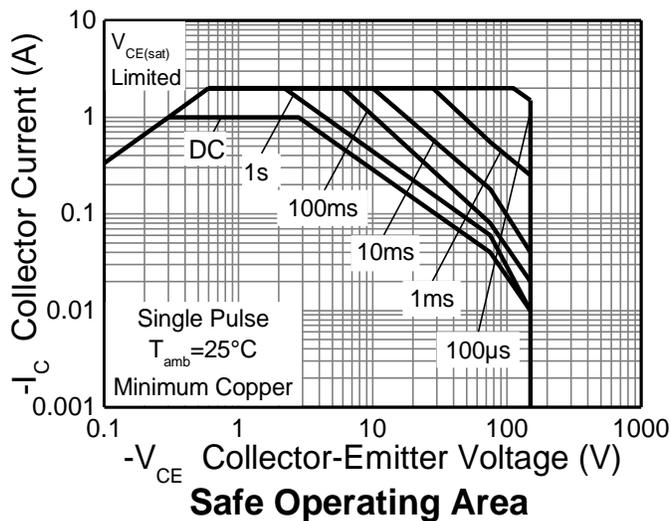
| Characteristic | Symbol | Value | Unit |
|---|-----------------------------------|-------------|------|
| Power Dissipation | P _D | 3 | W |
| | | 2 | |
| | | 1.6 | |
| | | 1.2 | |
| Thermal Resistance, Junction to Ambient | R _{θJA} | 41.7 | °C/W |
| | | 62.5 | |
| | | 78.1 | |
| | | 104 | |
| Thermal Resistance, Junction to Leads | R _{θJL} | 12.9 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

ESD Ratings (Note 10)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | C |

- Notes:
- For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 - Same as Note 5, except the device is mounted on minimum recommended pad layout.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

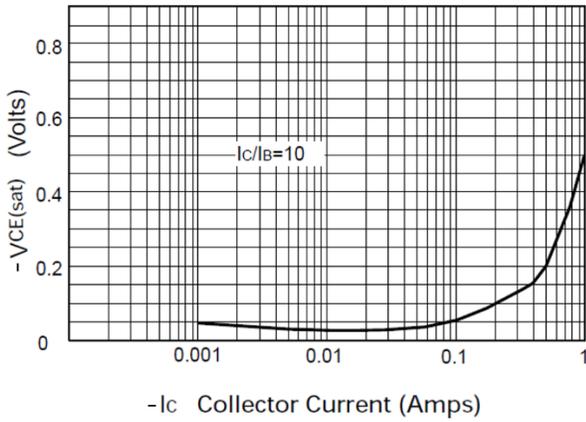


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

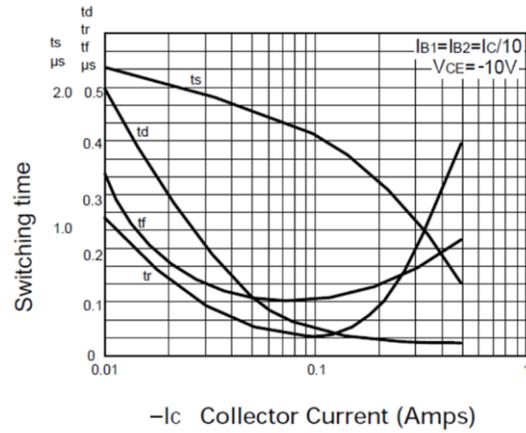
| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition | |
|--|----------------------|------|-----|------|------|---|--|
| Collector-Base Breakdown Voltage | BV _{CBO} | -150 | - | - | V | I _C = -100μA | |
| Collector-Emitter Breakdown Voltage (Note 11) | BV _{CEO} | -150 | - | - | V | I _C = -10mA | |
| Emitter-Base Breakdown Voltage | BV _{EBO} | -7 | - | - | V | I _E = -100μA | |
| Collector Cut-Off Current | I _{CBO} | - | -1 | -100 | nA | V _{CB} = -125V | |
| Emitter Cut-Off Current | I _{EBO} | - | -1 | -100 | nA | V _{EB} = -6V | |
| Collector-Emitter Saturation Voltage (Note 11) | V _{CE(sat)} | - | - | -0.5 | V | I _C = -500mA, I _B = -50mA | |
| | | | | -0.5 | | I _C = -1A, I _B = -200mA | |
| Base-Emitter Saturation Voltage (Note 11) | V _{BE(sat)} | - | - | -1.1 | V | I _C = -500mA, I _B = -50mA | |
| Base-Emitter Turn-On Voltage (Note 11) | V _{BE(on)} | - | - | -1.0 | V | I _C = -500mA, V _{CE} = -5V | |
| DC Current Gain (Note 11) | h _{FE} | - | - | - | - | I _C = -10mA, V _{CE} = -5V | |
| | | | | 50 | | 300 | I _C = -500mA, V _{CE} = -5V |
| | | | | 20 | | - | I _C = -1A, V _{CE} = -5V |
| Current Gain-Bandwidth Product | f _T | 30 | - | - | MHz | I _C = -10mA, V _{CE} = -20V, f = 20MHz | |
| Output Capacitance | C _{obo} | - | - | 20 | pF | V _{CB} = -10V, f = 1MHz | |

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%.

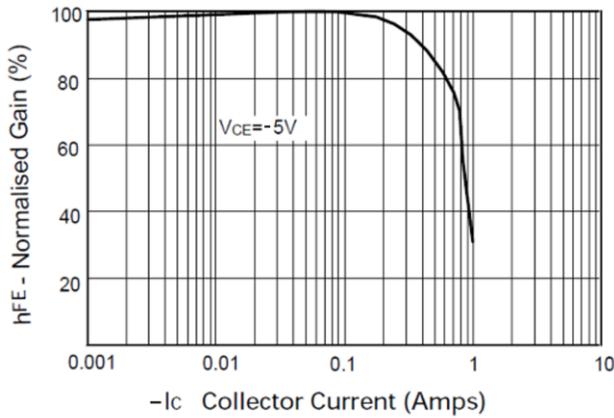
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



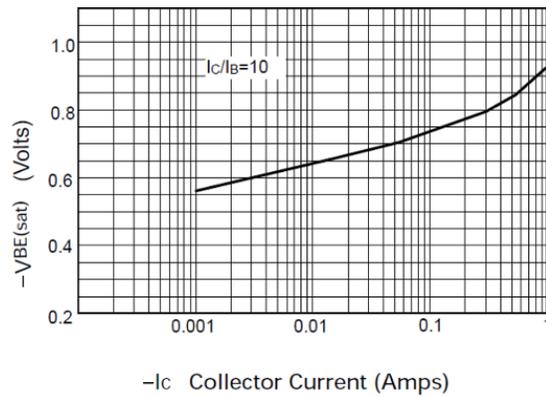
VCE(sat) v IC



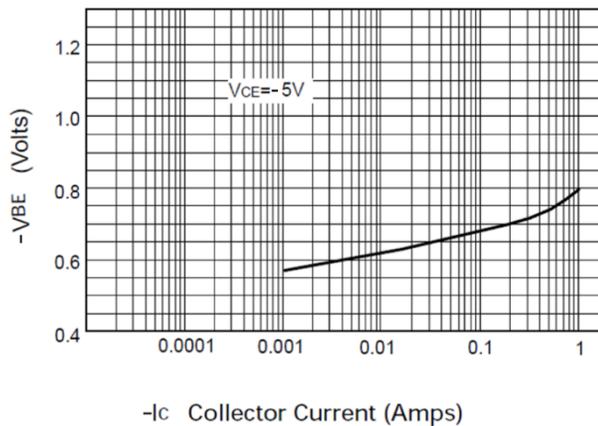
Switching Speeds



hFE v IC

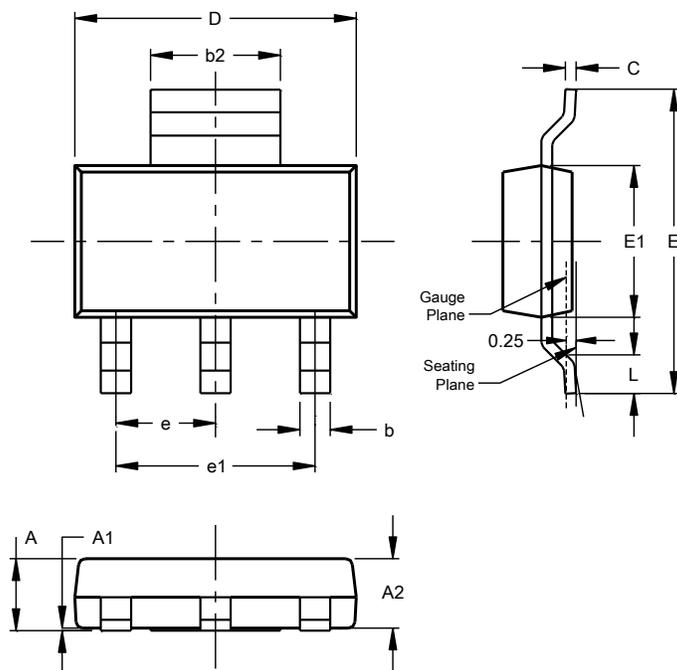


VBE(sat) v IC



VBE(on) v IC

Package Outline Dimensions

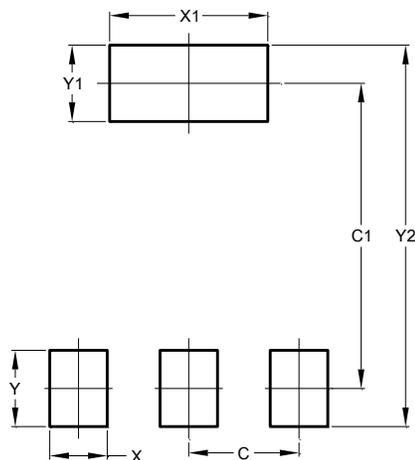


| SOT223 (Type DN) | | | |
|------------------|------|------|------|
| Dim | Min | Max | Typ |
| A | -- | 1.70 | -- |
| A1 | 0.01 | 0.15 | -- |
| A2 | 1.50 | 1.68 | 1.60 |
| b | 0.60 | 0.80 | 0.70 |
| b2 | 2.90 | 3.10 | -- |
| c | 0.20 | 0.32 | -- |
| D | 6.30 | 6.70 | -- |
| E | 6.70 | 7.30 | -- |
| E1 | 3.30 | 3.70 | -- |
| e | -- | -- | 2.30 |
| e1 | -- | -- | 4.60 |
| L | 0.85 | -- | -- |

All Dimensions in mm

Suggested Pad Layout

SOT223 (Type DN)



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 2.30 |
| C1 | 6.40 |
| X | 1.20 |
| X1 | 3.30 |
| Y | 1.60 |
| Y1 | 1.60 |
| Y2 | 8.00 |